

ABSTRACT OF THE DISCLOSURE

1 A semiconductor device (10) and its production method is disclosed in which a cap
2 film for a wiring made of copper or a copper alloy may prevent or reduce stress corrosion
3 cracking in the wiring. A semiconductor device (10) may include a wiring (11) made of
4 copper or a copper alloy including a barrier film (12) formed between the wiring (11) and a
5 cap film (13) for preventing copper diffusion. The barrier film (12) may include a SiC film
6 to provide an exposure prevention film, which prevents the wiring (11) from being exposed
7 to a film forming gas for the cap film (13), which includes a SiCN film.